

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning at page 5, line 32, with the following amended paragraph:

An alkaline compound used for this purpose includes alkaline metal hydroxides such as potassium hydroxide, sodium hydroxide, lithium hydroxide, etc.; alkaline metal carbonate such as potassium hydrogen carbonate, potassium carbonate, sodium hydrogen carbonate, lithium hydrogen carbonate, lithium ~~hydrogen~~ carbonate, etc.; aqueous ammonia solution or a salt thereof such as ammonium hydrogen carbonate, ammonium carbonate, etc.; piperazine (any of anhydrous or six hydrates), or a derivative thereof such as 1-(2-aminoethyl)piperazine, N-methylpiperazine, etc.; guanidine or a salt thereof such as guanidine carbonate, etc. They may be used alone or optionally in combination of two or more compounds.

Please replace the paragraph beginning at page 12, line 19, with the following amended paragraph:

Pure water was added to liquid cleaners compositions No.1 to No. [[9]] 6 of the present invention described in Table 1 to prepare a solution diluted to 10 to 100 times, in which the silicon wafer above prepared was dipped at 5°C for 5 minutes for washing. After rinsing with ultra-pure water and drying with a spin dryer, Amounts of impurity metals remained at the silicon wafer surface was quantitatively measured by the above-described method. Results are shown in Table 1.

Please replace the paragraph beginning at page 12, line 26, with the following amended paragraph:

Comparative Example 1

Silicon wafer contaminated with Fe, Cu, Al and Ca, prepared similarly as in Example 1 was dipped in solution obtained by diluting to 10 to 100 times with adding a treatment agent having composition of No. 7 to No. 11 described in Table 1 to pure water, or ultra-pure water (No. 12) at 25°C for 5 minutes for cleaning, followed by treatment similarly as in Example 1. Results are shown in Table 1.

Please replace the paragraph beginning at page 13, line 4, after Table 1, with the following amended paragraph:

Example 2

In cleaning silicon wafer contaminated with Fe, Cu, Al and Ca, prepared similarly as in Example 1, by brush-scrub cleaning using a brush made of polyvinyl alcohol, a solution obtained by diluting to 10 to 100 times with adding the liquid cleaner of the present invention having each composition of No. 13 to No. 16 described in Table 2 to pure water was sprayed. Treatment temperature was at 25°C and cleaning time was for 1 minute. After cleaning, silicon wafer was rinsed with ultra-pure water, followed by drying with a spin dryer, amounts of impurity metals remained at the silicon wafer surface was measured by the similar method as in Example 1. Results are shown in Table 2.

Please replace the paragraph beginning at page 14, line 4, with the following amended paragraph:

Comparative Example 2

In cleaning silicon wafer contaminated with Fe, Cu, Al and Ca, prepared similarly as in Example 1, by brush-scrub cleaning using a brush made of polyvinyl alcohol, a solution obtained by diluting to 10 to 100 times with adding a liquid cleaner having composition of No. 17 to No. 19 described in Table 2 to pure water or ultra-pure water (No. 20) was sprayed and treated similarly as in Example 2. Then, amounts of impurity metals remained at the silicon wafer surface was measured by similar method as in Example 1. Results are shown in Table 2.

Please replace the paragraph beginning at page 15, line 1, with the following amended paragraph:

Example 3

Cu wiring is used in the next generation semiconductor. In this case, to study damage of Cu wiring by cleaning agent used in cleaning based on Cu dissolution amount, liquid cleaners No. 21 to No. 24 of the present invention described in Table 3 was diluted to 10 to 100 times by adding pure water. Cu plated film was dipped in thus obtained solutions at 25°C for 30 minutes to measure an amount of dissolved Cu ions by an ICP-AES method. Amounts of dissolved Cu are shown in Table 3. These amounts correspond to damage degree to Cu wiring.

Please replace the paragraph beginning at page 15, line 9, with the following amended paragraph:

Comparative Example 3

The liquid cleaners shown by No. 25 to No. 27 in Table 3 were prepared by replacing a chelating agent of the present invention with EDTA and DTPA, which were diluted 10

to 100 times by adding pure water. Cu plated film was dipped in thus prepared solutions at 25°C for 30 minutes to measure amount of corroded and dissolved Cu ions by an ICP-AES method. Results are shown in Table 3.